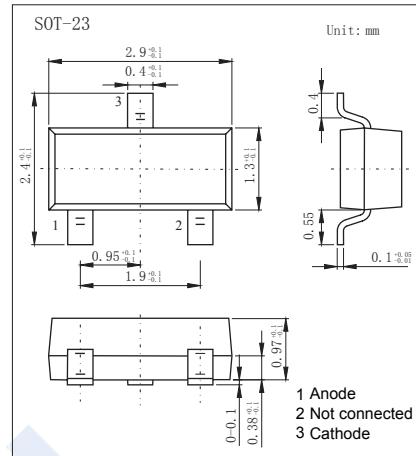
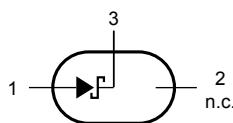


Schottky Diodes

BAT720 (KAT720)

■ Features

- Ultra high switching speed
- Low forward voltage
- Guard ring protected



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Reverse Voltage	V _{RM}	40	V
Forward Current	I _F	500	mA
Peak Forward Surge Current tp < 10 ms	I _{FM}	2	A
Thermal Resistance Junction to Ambient	R _{θ JA}	500	°C/W
Junction Temperature	T _J	125	
Storage Temperature range	T _{stg}	-65 to 150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V _R	I _R = 100 uA	40			V
Forward voltage	V _F	I _F = 500mA			550	mV
Reverse voltage leakage current	I _R	V _R = 35 V			100	uA
		V _R = 35 V, T _J = 100°C			10	mA
Junction capacitance	C _d	V _R = 0 V, f= 1 MHz	60		90	pF

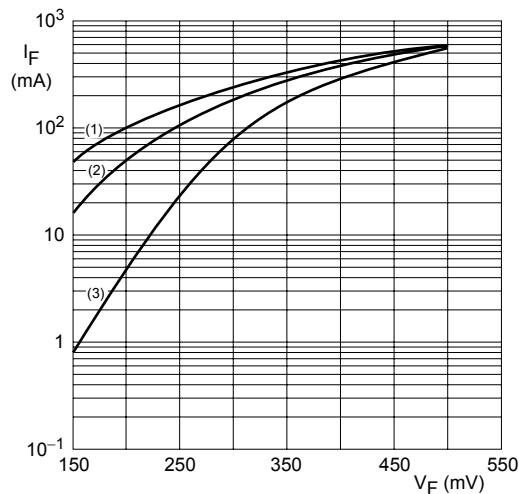
■ Marking

Marking	L6*
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Schottky Diodes

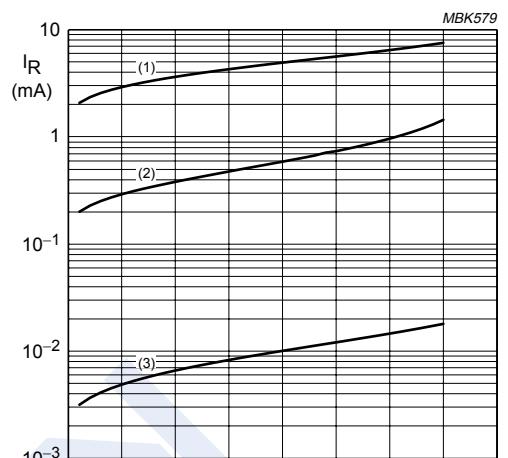
BAT720 (KAT720)

■ Typical Characteristics



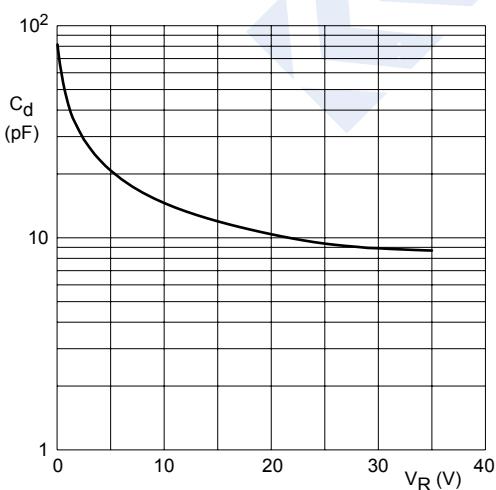
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.2 Forward current as a function of forward voltage; typical values.



- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



$f = 1\text{ MHz}; T_j = 25\text{ }^{\circ}\text{C}$.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.